

RJP4003ASA

Nch IGBT for Strobe Flash

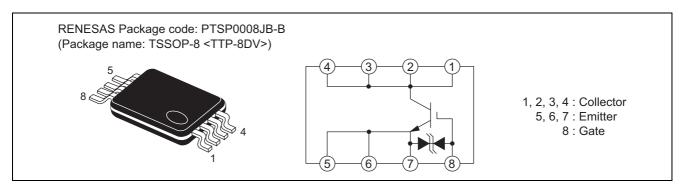
REJ03G1475-0200 Rev.2.00 Nov 10, 2008

Features

• Small surface mount package (TSSOP-8)

V_{CES}: 400 V
 I_{CM}: 150 A
 Drive voltage: 4 V

Outline



Applications

Strobe flash for cameras

Maximum Ratings

 $(Tc = 25^{\circ}C)$

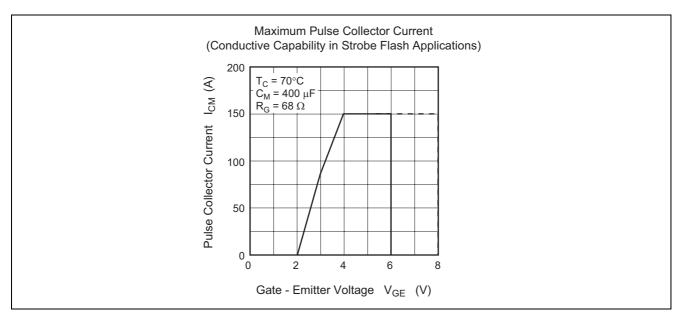
Parameter	Symbol	Ratings	Unit	Conditions
Collector-emitter voltage	V _{CES}	400	V	$V_{GE} = 0 V$
Gate-emitter voltage	V_{GES}	±6	V	V _{CE} = 0 V
Peak gate-emitter voltage	V_{GEM}	±8	V	$V_{CE} = 0 \text{ V}, \text{ tw} = 10 \text{ s}$
Collector current (Pulse)	I _{CM}	150	Α	$C_{M} = 400 \ \mu F$
				(see performance curve)
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	

Electrical Characteristics

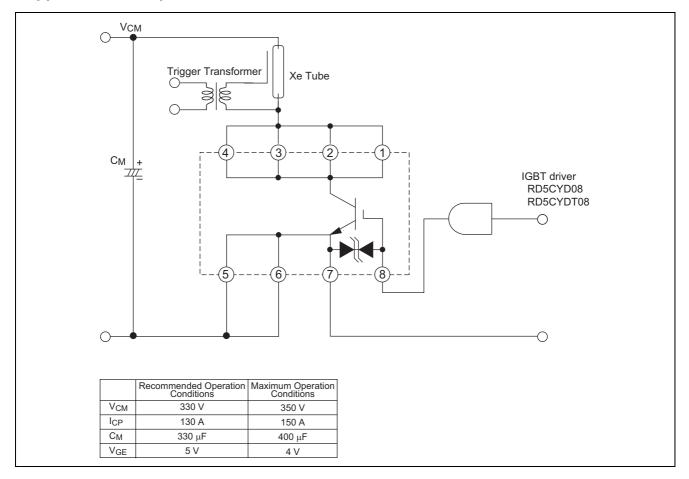
 $(Tj = 25^{\circ}C)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions
Collector-emitter breakdown voltage	$V_{(BR)CES}$	450	_	_	V	$I_C = 1 \text{ mA}, V_{GE} = 0 \text{ V}$
Collector-emitter leakage current	I _{CES}	_	_	10	μΑ	$V_{CE} = 400 \text{ V}, V_{GE} = 0 \text{ V}$
Gate-emitter leakage current	I _{GES}	_	_	±10	μΑ	$V_{GE} = \pm 6 \text{ V}, V_{CE} = 0 \text{ V}$
Gate-emitter threshold voltage	$V_{GE(th)}$	0.5	0.7	1.5	V	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$
Collector-emitter saturation voltage	V _{CE(sat)}	_	5.0	10.0	V	I _C = 150 A, V _{GE} = 4 V
Input capacitance	Cies	_	5000	_	pF	$V_{CE} = 25 \text{ V}, V_{GE} = 10 \text{ V},$
						f = 1MHz

Performance Curves



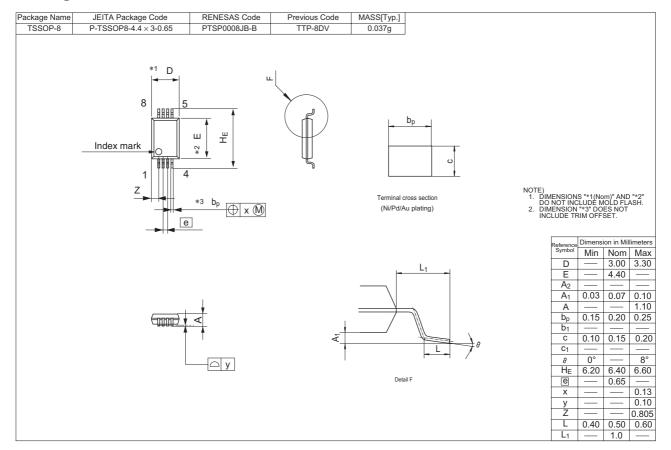
Application Example



Precautions on Usage

- 1. IGBT has MOS structure and its gate is insulated by thin silicon oxide. So please handle carefully to protect the device from electrostatic charge.
- 2. Gate drive voltage during on-period must be applied to satisfy the rating of maximum pulse collector current. And turn-off dv/dt must become less than 400 V/ μ s. In general, when $R_{G \text{ (off)}} = 68 \Omega$, it is satisfied.
- 3. For safety use, we recommend that the ground of the drive signal is connected to pin 7.
- 4. The operation life should be endured until repeated discharge of 5,000 times under the charge current ($I_{Xe} \le 150~A$: full luminescence condition) of main capacitor ($C_M = 400~\mu F$). Repetition period under full luminescence condition is over 3 seconds.
- 5. Total operation hours applied to the gate-emitter voltage must be within 5,000 hours when V_{GE} is driven at 6 V.

Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – 00 – Q0	RJP4003ASA-0-Q0

Note: Please confirm the specification about the shipping in detail.

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